

Abstracts

A sub 1-V SOI CMOS low noise amplifier for L-band applications

H. Komurasaki, H. Sato, N. Sasaki, K. Ueda, S. Maeda, Y. Yamaguchi and T. Miki. "A sub 1-V SOI CMOS low noise amplifier for L-band applications." 1998 Radio Frequency Integrated Circuits (RFIC) Symposium 98. (1998 [RFIC]): 153-156.

This paper describes a sub 1.0 V low noise amplifier in a 0.35 μm SOI (silicon on insulator) CMOS process. Active-body control enables a sub 1.0 V operation, and improves gain and the 1 dB-compression point. The gain of 7.0 dB, the NF of 3.6 dB and the input 1 dB-compression point of -4.5 dBm are obtained at 1.0 V and 1.9 GHz.

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